
2SK2315

Silicon N-Channel MOS FET

HITACHI

Application

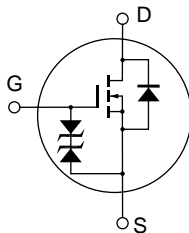
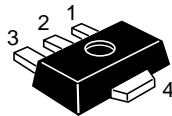
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 2.5 V gate drive device can be driven from 3 V source.
- Suitable for DC-DC converter, motor drive, power switch, solenoid drive

Outline

UPAK



1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings (Ta = 25°C)

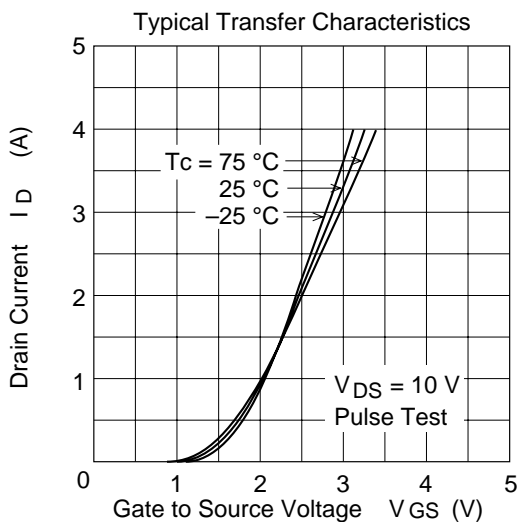
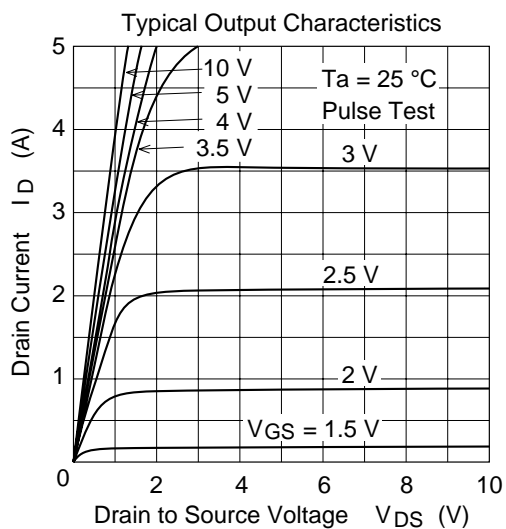
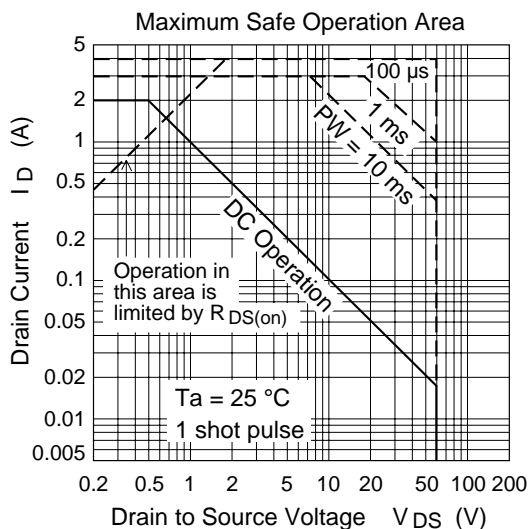
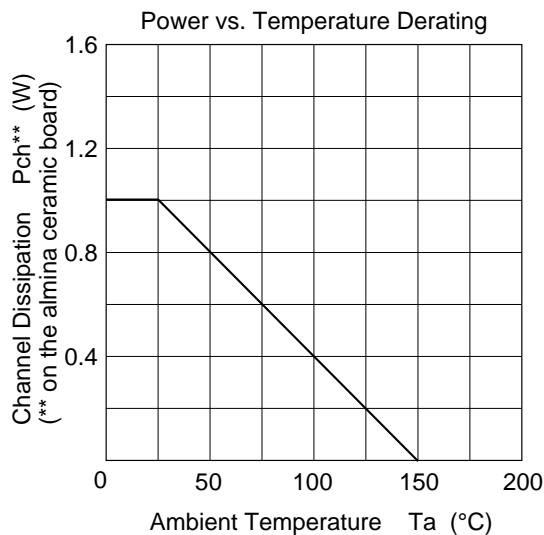
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	2	A
Drain peak current	$I_{D(pulse)}^{*1}$	4	A
Body to drain diode reverse drain current	I_{DR}	2	A
Channel dissipation	Pch^{*2}	1	W
Channel temperature	Tch	150	°C
Storage temperature	$Tstg$	-55 to +150	°C

- Notes
1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$
 2. When using the alumina ceramic board (12.5 × 20 × 0.7mm)
 3. Marking is "TY"

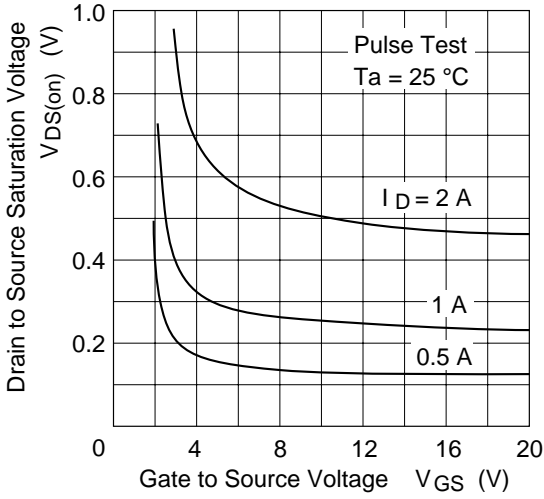
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±5	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	5	μA	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.5	—	1.5	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.4	0.6	Ω	$I_D = 0.3 \text{ A}$ $V_{GS} = 3 \text{ V}^{*1}$
		—	0.35	0.45	Ω	$I_D = 1 \text{ A}$ $V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	1.5	1.8	—	S	$I_D = 1 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	173	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	85	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	23	—	pF	$f = 1 \text{ MHz}$
Turn-on time	t_{on}	—	21	—	ns	$I_D = 1 \text{ A}$, $R_L = 30 \Omega$
Turn-off time	t_{off}	—	85	—	ns	$V_{GS} = 10 \text{ V}$

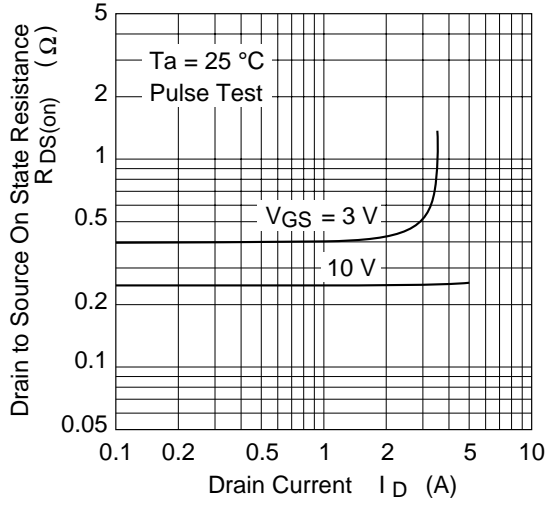
Note 1. Pulse Test



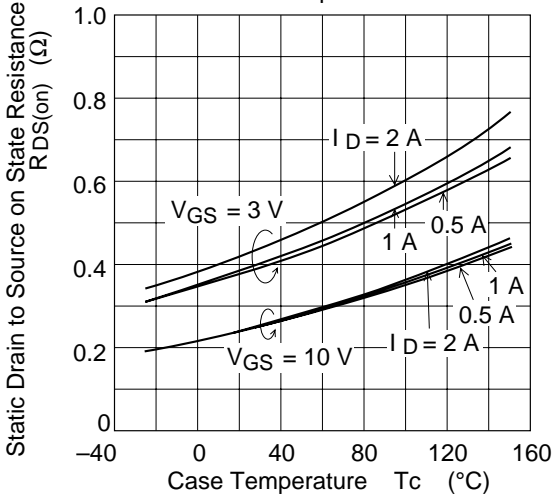
Drain to Source Saturation Voltage vs. Gate to Source Voltage



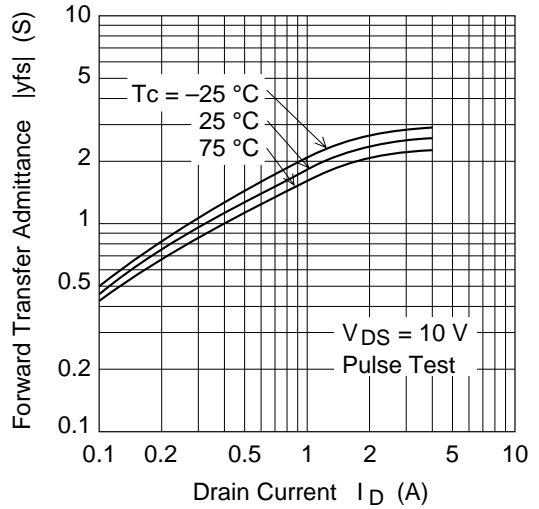
Static Drain to Source State Resistance vs. Drain Current



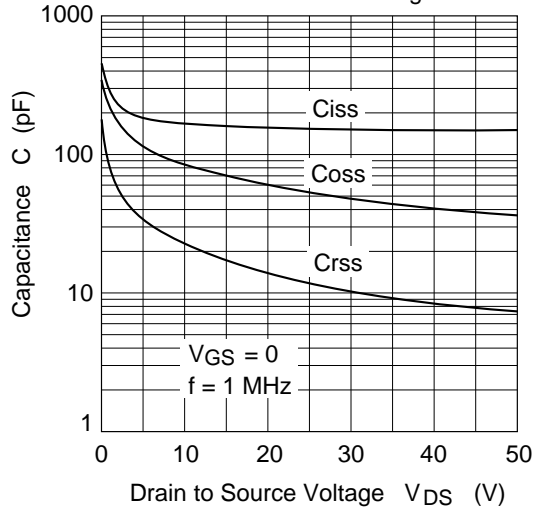
Static Drain to Source on State Resistance vs. Temperature



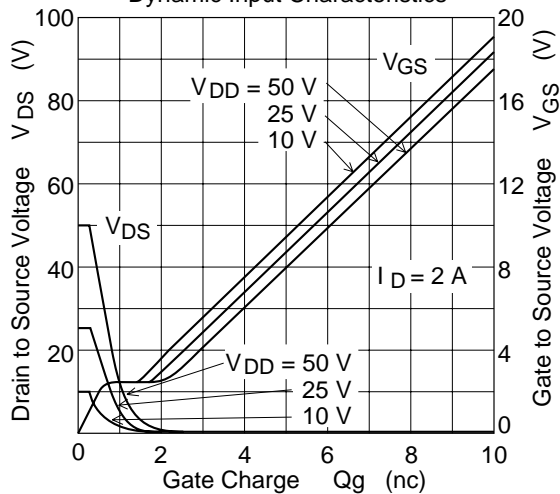
Forward Transfer Admittance vs. Drain Current



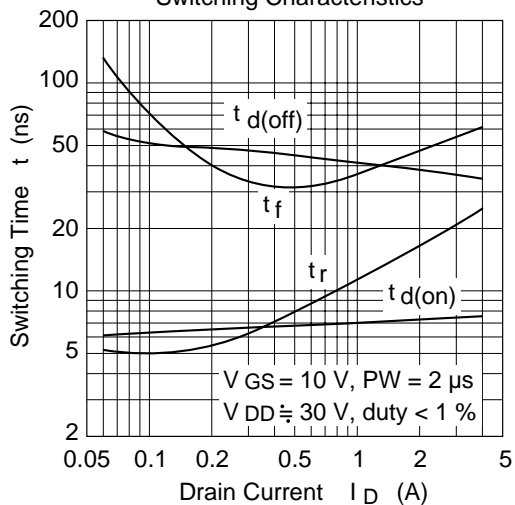
Typical Capacitance vs. Drain to Source Voltage



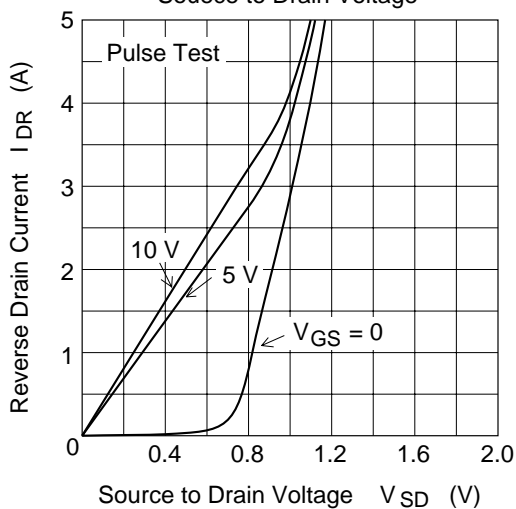
Dynamic Input Characteristics

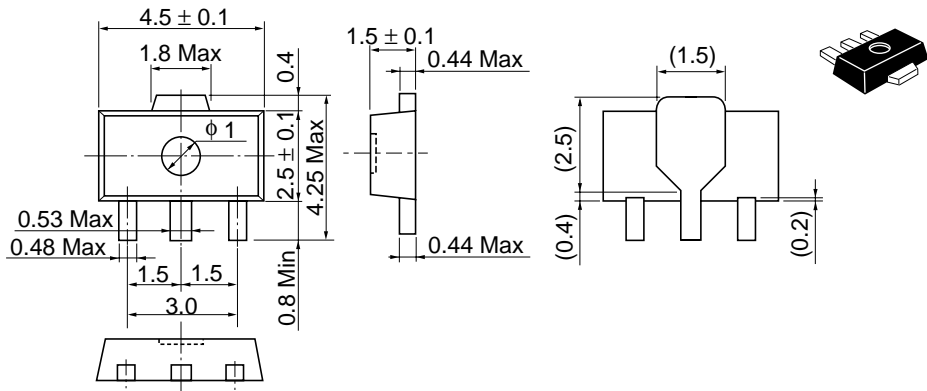


Switching Characteristics



Reverse Drain Current vs. Source to Drain Voltage





Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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